FÖRM PTO-892 U.S. DEPARTMENT OF COMMERCE (REV. 3-78) PATENT AND TRADEMARK OFFICE										458,507					2306			ATTACHMENT TO					
NOTICE OF REFERENCES CITED APPLICANT(S) Hori et al.																							
*	DOCUMENT NO. DATE												NAME				CI	ASS		UB- .ASS	FILING DATE IF		
*	A	4	7	239980 12-						-80	Ħ	Takanashi etal.					7	307 205					
×	В	1	4	8	2985				ł	<u>- 84</u>	1 7	Itohetal.					- 1-	365 226		ے۔۔۔ 'د			
	С	-			/\								CCXX 81.				Ť	<u></u>					
	D														, , ,	<u> </u>							
	ε																						
	F																						
	G																						
	н										<u> </u>											<u> </u>	
	1																						
	J						Ш												ļ				
:	κ																						
		г							г		FORE	IGN PA	ATENT	DOC	UMEN	TS				I		PERTI	NENT
*		DOCUMENT NO.						DATE			COUNTRY			NAME			CI	CLASS SUB			SHTS.	SPEC.	
	L			_		$\bot \bot \bot$					-												
	M																					 	
	N			_		Н				· · · · ·	-							-					-
	0			\dashv			Н				-		·					-		<u> </u>			
	P			\dashv			Н				\bot			-				-				-	-
	Q		}								. (1)				<u> </u>								
		<u> </u>	-, ,							ENCES											(10	<u>σ Λ 3</u>	
×	R	Itoh, K., et al. "An Experimental 1Mb DRAM with On-Chip Voltage Limiter", 1984 IEEE International Solia-State Circuits Conf., pp. 782-283.																					
			YUE	ry	di	Oric	31	<u> </u>	<u> </u>	Male 1	<u> </u>	<u> 1211</u>	<u>Org</u>	, pp.	۸۵۸	<u></u> ', X & &	2				· · · · · · · · ·		
	S											· · ·											
																	· · · · · ·						
	Т																		***				
																							_
	υ																						
EXA	11MA >	NEF	~	•	 1	-	7	_].		OATE	h s. k	97						_					
		_	<u>_</u>	æ	ber		<u></u>	<u> </u>	y of th	nis refe	rence	is no	t bein	g furn	ished	with th	nis of	fice a	ction				
							(5	See i	Manu	al of Pa	tent l	Exam	ining l	Proce	dure,	section	707.	05 (a	1).)				